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メタデータ	言語: English
	出版者:
	公開日: 2008-02-12
	キーワード (Ja):
	キーワード (En):
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URL	http://hdl.handle.net/10098/1582

Fundamental optical absorption of CsPbI₃ and Cs₄PbI₆

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Abstract

The fundamental optical absorption spectra of CsPbI₃ and Cs₄PbI₆ have been measured for the first time. There are distinct differences in the absorption characteristic between the two compounds: Cs₄PbI₆ exhibits strong, oscillator-like absorption and a prominent, blue-shifted excitonic peak, compared to the case of CsPbI₃. The differences are explainable in terms of whether the Pb²⁺(I⁻)₆ octahedra are weakly (CsPbI₃) or strongly (Cs₄PbI₆) mutually isolated in the respective compounds.

Keywords: B. CsPbl3; B. Cs4Pbl6; D. Fundamental absorption spectrum; D. Optical properties; D. Electronic states; Exciton

Although it has been known from old times that there are two stable ternary compounds in the binary system of CsI-PbI₂, namely, CsPbI₃ and Cs₄PbI₆ [1,2], little is known about the optical properties of the compounds. The only knowledge is that exciton absorption of CsPbI₃ [3–5] and Cs₄PbI₆ [5] lies at photon energies around 3.0 and 3.4 eV, respectively. The reason for such a poor knowledge on these compounds is probably due to difficulty in obtaining their specimens. For example, as reported in Ref. [1], it is difficult to obtain Cs₄PbI₆ in a pure state by melting CsI and PbI₂ together in the stoichiometric proportion. In the present work, we prepared specimens suitable for optical studies of CsPbI₃ and Cs₄PbI₆ by two different ways and observed intrinsic absorption spectra of these compounds for the first time.

In measuring the fundamental optical absorption spectrum of materials, it is necessary to prepare specimens of very thin films or crystallites dispersed in transparent matrices. Previously we showed that quench deposition of a mixture of metal halides (binary system) and subsequent annealing of the deposits are effective in obtaining clusters and/or ternary compounds of metal halides [6,7]. This was

indeed successfully applied to produce crystallites of Cs₄PbCl₆ in CsCl matrices [8]. Such specimens were favorably used to measure the fundamental absorption spectrum of Cs₄PbCl₆ because the host CsCl was transparent up to a considerable photon energy (about 6.8 eV). Therefore, in the present experiments, we first attempted to produce crystallites of CsPbI₃ and/or Cs₄PbI₆ in CsI matrices in a similar manner.

Fig. 1 shows the absorption spectra at 77 K of the binary $(CsI)_{1-x}(PbI_2)_x$ system with x = 0.4, 0.2 and 0.1. Here, the nominal x values of the mixtures of CsI and PbI2 were used to represent the composition in the system. According to elemental analyses carried out for several films by an electron probe X-ray micro-analyzer, the deviation of the composition ratios from the nominal ones was within 5% (to minimize the deviation, we deposited the films rapidly, at a rate of about 20 nm/min; such a high deposition rate was previously shown to be favorable for achieving nominal ratios in the films of mixed metal halides [9]). The spectral measurements were carried out in situ on the films quench deposited onto 77 K substrates (silica glass) and subsequently annealed at 400 K for 10 min, by the method [10] of simultaneous measurements of transmittance and reflectance of the films, from which accurate absorption structures were determined. In these spectra,

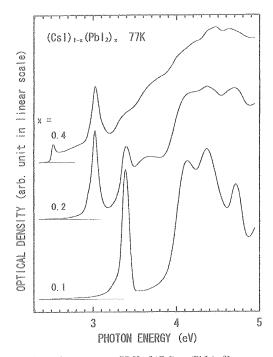


Fig. 1. Absorption spectra at 77 K of $(CsI)_{1-x}(PbI_2)_x$ films prepared by quench deposition onto 77 K substrates and subsequent annealing at 400 K for 10 min.

three characteristic absorption peaks were observed at 2.51, 3.02 and 3.38 eV, depending on the values of x. Of the three, the lowest-energy peak is due to exciton transitions in the PbI2 crystal. Other two peaks are also considered to be of excitonic origin in view of their very sharp absorption features. Therefore, we see that there are two different crystalline phases addressable as due to ternary compounds. They are considered to be CsPbI3 and Cs₄PbI₆. Indeed, the 3.02 eV peak corresponds to the reported CsPbI3 exciton absorption (peaking around 3.0 eV [3-5]), and the 3.38 peak, to the Cs₄PbI₆ exciton absorption (around 3.4 eV [5]). The film with x = 0.1 is considered to represent intrinsic absorption of Cs₄PbI₆, as compared with the reported absorption spectra in Ref. [5], where weak absorption due to CsPbI3 exciton transitions arose together with the Cs₄PbI₆ exciton absorption.

It was difficult to measure intrinsic absorption spectrum of CsPbI₃ using the films prepared from the mixture of CsI and PbI₂, because the CsPbI₃ phase always coexisted either with the PbI₂ phase (for 0.2 < x < 0.5) or with the Cs₄PbI₆ phase (for 0.1 < x < 0.3) as well as with the CsI phase. We note that the reported spectra [3,4] of the CsPbI₃ exciton absorption have only been presented in a very narrow photon energy region, from about 2.9 to about 3.2 eV, probably because of the same reason. Therefore, we employed an alternative preparation method of specimens, i.e. solid-state chemical reaction between the starting compounds. Such a method was shown, in the previous study of the CsCl-PbCl₂ system [8], to be effective in

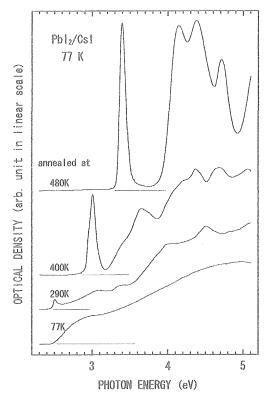


Fig. 2. The change in the absorption spectrum due to annealing of a PbI₂-deposited CsI crystal, measured in situ at 77 K for increasing annealing temperatures indicated.

dispersing crystallites of Cs₄PbCl₆ in the bulk crystal of CsCl. To apply the method to the present system of CsI–PbI₂, we prepared amorphous PbI₂ films (by quench deposition) on the polished surfaces of CsI bulk crystals cooled to 77 K and investigated the annealing behaviors of the prepared samples (PbI₂/CsI samples) by in situ optical absorption and reflection spectroscopy [10].

Figs. 2 and 3 show the changes of absorption and reflection spectra, respectively, due to annealing at various temperatures of a Pbl₂/CsI sample. For each annealing temperature, an in situ spectral measurement was carried out at 77 K. Heating and cooling in each annealing cycle were performed at rates of 1 and 10 K/min, respectively, and the annealing time was 10 min for each. The spectrum labeled 77 K was obtained for the as-deposited Pbl₂ film. Then the Pbl₂/CsI sample was subject to the first annealing cycle of annealing temperature 290 K. Other spectra in the figure were obtained for subsequent cycles at the annealing temperatures indicated.

The spectra labeled 77 K very well reproduces earlier results [11] on amorphous PbI_2 films (which was characterized by missing exciton absorption). Exciton absorption (at 2.51 eV) of PbI_2 was observed in the sample annealed at 290 K for both the absorption and reflection spectra, indicating that the amorphous PbI_2 was transformed to the crystalline state.

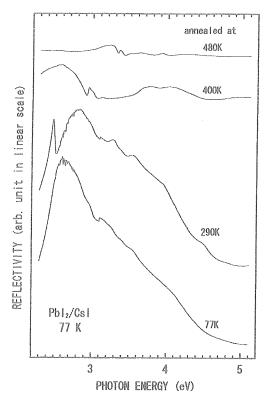


Fig. 3. The change in the reflection spectrum due to annealing of a PbI₂-deposited CsI crystal, measured in situ at 77 K for increasing annealing temperatures indicated.

When the sample was annealed at 400 K, the absorption spectrum exhibited a prominent peak at 3.02 eV. The peak can be assigned as due to CsPbI3 exciton, considering the energetic position. Unlike the absorption spectra of the $(CsI)_{1-x}(PbI)_x$ films with x = 0.2 and/or 0.4 (Fig. 1), this spectrum showed no trace of excitonic absorption of PbI2 nor of Cs₄PbI₆. The crystalline PbI₂ that had existed on the surface of the CsI crystal was considered to have reacted chemically with CsI completely by the annealing (at 400 K), yielding CsPbI₃. Therefore, the spectrum is attributed to intrinsic absorption of CsPbI3. It should be noted here that the corresponding reflection spectrum (curve 400 K in Fig. 3) exhibited only a weak structure at energies around 3 eV, despite the strong CsPbI3 exciton absorption around the same energies (Fig. 2, curve 400 K). This suggests that the CsPbI3 products are embedded in the bulk, but near the surface, of the CsI crystal, forming crystallites. It seems impossible to produce a layer purely composed of CsPbI3 only, but instead, a mixed phase of CsPbI3 and CsI was achieved, from which we were able to obtain the fundamental absorption spectrum of CsPbI3 for the first time.

On annealing the sample at a higher temperature, 480 K, a further, drastic change occurred in the spectral structure, as seen from curve 480 K in Fig. 2. The resulting absorption spectrum was quite the same in outline as that (curve 0.1 in

Fig. 1) of Cs₄PbI₆. This means that a further chemical reaction occurred between the above-produced CsPbI₃ crystallites and the CsI environment in the CsI crystal, yielding the crystallites of Cs₄PbI₆. The new crystallites were also embedded in (and not 'on' the surface of) the bulk CsI crystal, as seen from the very weak structures in the corresponding reflection spectrum (curve 480 K in Fig. 3) throughout the measured energy region (compared with the marked absorption structures in curve 480 K in Fig. 2).

As seen from Fig. 2, Cs₄PbI₆ exhibited strong, oscillatorlike absorption and a prominent, blue-shifted exciton peak, compared with the case of CsPbI3. These characteristics may be explained as follows. Low-energy fundamental optical absorption of CsPbI3 and Cs4PbI6 crystals may be dominated by electronic transitions from 6s to 6p states in the Pb²⁺-ion sublattice, as in the case of PbI₂ crystals [12]. Both the crystals of CsPbI3 and Cs4PbI6 are built up of nearly regular Pb2+(I-)6 octahedra with Pb2+ ions located at their centers [1,2]. In CsPbI₃, however, each I⁻ ion is shared between two adjacent octahedra, while, in Cs₄PbI₆, adjacent octahedra are separated by intervening Cs+. Therefore, in Cs₄PbI₆ the dilution of the sublattice by the intervening Cs⁺ ions may have the effect of preventing the Pb2+ electronic states from forming extended states. To a first approximation, these states may form a set of localized states confined to within the individual Pb2+(I-)6 octahedra. Due to the localized nature of both the Pb 6s and 6p states, the 6s to 6p electronic transitions may result in a large oscillator strength in a narrow energy range. This is favorable for understanding the strong absorption intensities, as well as the enhanced (first) exciton absorption, of Cs₄PbI₆. The localization of both the Pb 6s and 6p states has the effect of confining the exciton created in the Pb2+-ion sublattice, thus giving the reason for the blue shift of the exciton energy of Cs₄PbI₆ with respect to that of CsPbI₃.

The localized nature of, and thus the absorption structures related to, the Pb 6s and 6p states in Cs₄PbI₆ is rather similar to the case of isolated Pb2+ ions doped in fcc alkali halide crystal, where the Pb2+ ions are located at the centers of octahedral quasi-complexes Pb2+(I-)6. For example, in Pb2+-doped KI crystals, the lowest-energy absorption band (named A band, coming from spin-orbit allowed ¹A_{1g} to ³T_{1u} transitions) is observed at 3.6 eV, and the second band (C band, dipole-allowed 1A1g to 1T1u transitions) at 4.5 eV, together with a weak shoulder (B band, vibration-induced ¹A_{1g} to ³T_{2u} or ³E_u transitions) at energy between the two bands, around 4.2 eV [13]. However, the spectral structures of Cs₄PbI₆ does not so well resemble any of the reported spectra of Pb²⁺-doped fcc alkali iodides [14-17]. The main reason for this is probably due to the associated charge-compensating Cs+-ion vacancies in the latter case.

Fig. 4 compares the absorption spectrum of Cs₄PbI₆ with that [18] of (CH₃NH₃)₄PbI₆·2H₂O. There is a striking resemblance in the spectral structures and their energetic positions between the two compounds, i.e. between

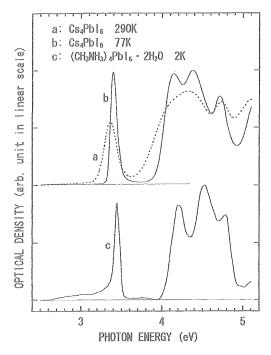


Fig. 4. The absorption spectra of Cs₄PbCl₆ measured at 77 K (a) and 290 K (b) are compared with that of (CH₃NH₃)₄PbI₆·2H₂O measured at 2 K (c). The latter spectrum is cited from Ref. [18], where the absorption spectrum was deduced from a reflection spectrum.

spectrum b, measured at 77 K for Cs_4PbI_6 and spectrum c, measured at 2 K for $(CH_3NH_3)_4PbI_6\cdot 2H_2O$ (in Ref. [18], spectrum c was deduced from a reflection spectrum through the Kramers–Kronig analysis); in the latter compounds, octahedral $Pb^{2+}(I^-)_6$ clusters are nearly isolated (by the countercations $(CH_3NH_3)^+$), similar to the case of Cs_4PbI_6 . Therefore, a similar spectral-structures assignment described for $(CH_3NH_3)_4PbI_6\cdot 2H_2O$ in Ref. [18], where the fine absorption structures in the region 4–5 eV are attributed to crystal-field splitting of the C band due to deviation from O_h symmetry of the $Pb^{2+}(I^-)_6$ clusters, may be applicable to Cs_4PbI_6 . In the spectrum a, measured at 290 K for Cs_4PbI_6 , the vibration-induced nature of the B band is indeed evidenced by the enhanced absorption intensities at around 3.9 eV.

In conclusion, it was difficult to prepare the films of the ternary compounds of CsPbI₃ and Cs₄PbI₆ purely composed of a single phase of the compounds. However, it was possible to disperse crystallites of these compounds separately in a CsI environment by making use of solid-state chemical reaction between CsI and PbI₂ of PbI₂-deposited CsI bulk crystals. Using such specimens, we measured the fundamental optical absorption spectra of

CsPbI₃ and Cs₄PbI₆ for the first time. The spectra showed distinct differences in the structure between the two compounds. The differences are explainable in terms of whether the Pb²⁺(I⁻)₆ octahedra are weakly (CsPbI₃) or strongly (Cs₄PbI₆) mutually isolated in the respective compounds.

We are now developing a novel method for determining optical constants of crystallites dispersed in, or near the surface of, a transparent crystal. The method is applicable to the present system. Detailed discussions of the absorption characteristics of the CsPbI₃ and Cs₄PbI₆ crystallites will be reported later, including the determination of oscillator strengths and/or effective numbers of electrons contributing to their optical absorption, and also including the comparison with the chlorides, i.e. CsPbCl₃ and Cs₄PbCl₆ obtained for the previous, CsCl-PbCl₂ system.

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